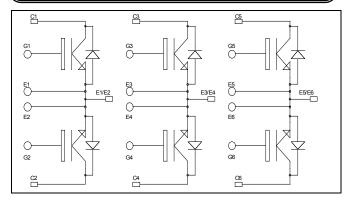


Triple Dual Common Source Trench + Field Stop IGBT3 Power Module



$$V_{CES} = 1700V$$

 $I_C = 50A$ @ $Tc = 80$ °C

Application

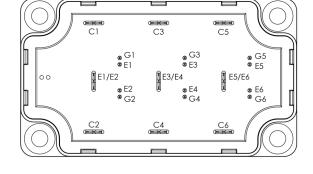
- **AC Switches**
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Kelvin emitter for easy drive

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- **RoHS Compliant**



Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	70	
$I_{\rm C}$	Continuous Conector Current	$T_C = 80$ °C	50	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	310	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 125^{\circ}C$	100A @ 1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings @ $T_i = 25^{\circ}$ C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		2.0	2.4	V
$V_{CE(sat)}$		$I_C = 50A$	$T_{j} = 125^{\circ}C$		2.4		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1 \text{mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$\begin{aligned} V_{GE} &= 0V \\ V_{CE} &= 25V \\ f &= 1MHz \end{aligned}$			4400		
C_{oes}	Output Capacitance				180		pF
C_{res}	Reverse Transfer Capacitance				150		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			370		
T_{r}	Rise Time	$V_{GE} = 15V$			40		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 900V$ $I_C = 50A$ $R_G = 10\Omega$			650		ns
T_{f}	Fall Time				180		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 900V$ $I_C = 50A$			400		ns
T_{r}	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				800		
T_{f}	Fall Time	$R_G = 10\Omega$			250		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 900V$	$T_j = 125$ °C		16		I em
E_{off}	Turn-off Switching Energy	$I_{\rm C} = 50 A$ $R_{\rm G} = 10 \Omega$	$T_j = 125$ °C		15		mJ

Diode ratings and characteristics

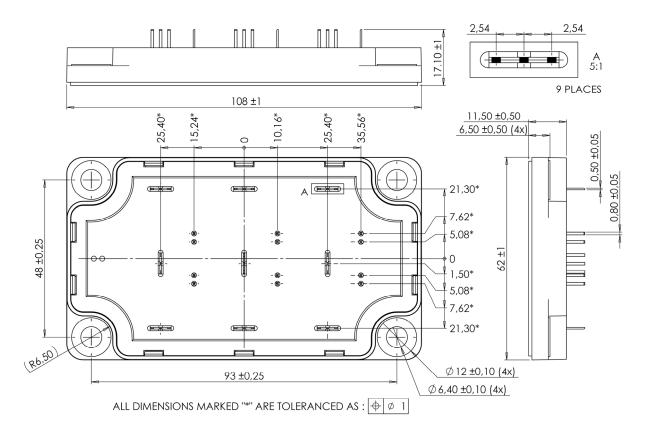
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
Ţ	Maximum Reverse Leakage Current	V _R =1700V	$T_j = 25^{\circ}C$			250	^
I_{RM}			$T_{j} = 125^{\circ}C$			500	μA
I_F	DC Forward Current		$Tc = 80^{\circ}C$		50		A
V_{F}	Diode Forward Voltage	$I_F = 50A$	$T_i = 25^{\circ}C$		1.8	2.2	V
V F	Diode i of ward voltage		$T_i = 125^{\circ}C$		1.9		•
t _{rr}	Reverse Recovery Time	,	$T_j = 25^{\circ}C$		385		ns
۲rr			$T_{j} = 125^{\circ}C$		490		113
0	Davanga Dagayany Changa	$I_F = 50A$ $V_R = 900V$ $di/dt = 800A/\mu s$	$T_j = 25^{\circ}C$		14		uС
Q_{rr}	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		23		μС
Е	Reverse Recovery Energy	. T _j =	$T_j = 25$ °C		6		mJ
$E_{\rm r}$			$T_i = 125$ °C		12		111J



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance		IGBT			0.4	°C/W
R_{thJC}			Diode			0.7	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

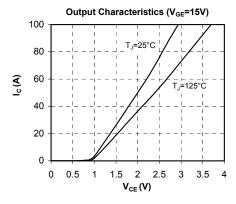
SP6-P Package outline (dimensions in mm)

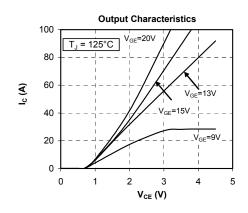


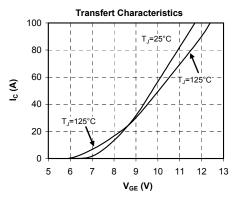
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

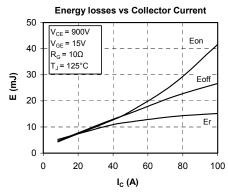


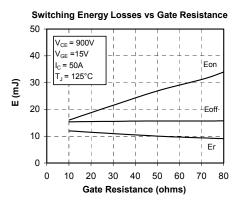
Typical Performance Curve

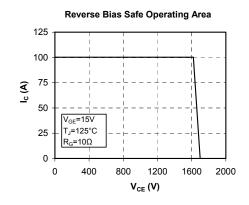


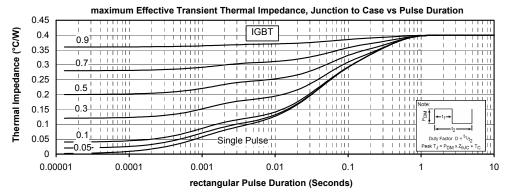






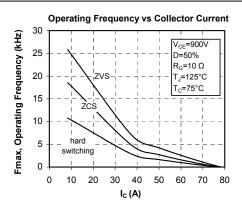


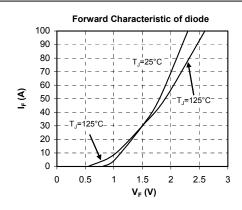


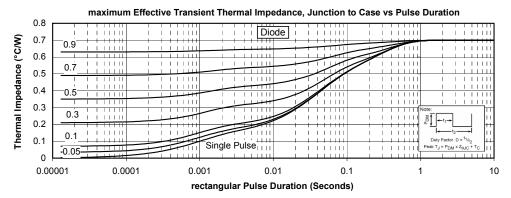


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